

consisting of positive photosensitive organic material, negative photosensitive organic material, silicon oxide, silicon nitride, and silicon nitride oxide.

55 (New). A method according to claim 29,

wherein the EL display device is combination with an electronic apparatus,

wherein the electronic apparatus is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a navigation system for vehicles, a personal computer, and a portable information terminal.--

REMARKS

We are in receipt of the Office Action dated October 17, 2001, and the accompanying Amendment and following remarks are made in light thereof.

In the Office Action, the Examiner objected to the specification and requested that the cross-reference to the parent application appearing on page 1 of the specification be amended to recite the patent number of the parent application. This has been done in the accompanying Amendment.

Claims 29-38 are pending in this application. Pursuant to the Office Action, each of these claims is rejected under 35 USC 101 for "same invention" double patenting over U.S. Patent No. 6,246,070 issuing from the parent application. Applicant believes that the Amendment to Claims 29, 30, and 33-36 presented herein overcomes this rejection. New claims 29-55 are also being added in the present Amendment to more fully claim the invention.

Accordingly, Applicant respectfully submits that the claims pending in this application are allowable, and an early Office Action in this regard is earnestly solicited.

Respectfully submitted,

A handwritten signature in dark ink, appearing to read "Stephen B. Heller", is written over a horizontal line.

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend claims 29, 30, 33-36 to read as follows:

29 (Amended). A method of fabricating an EL display device, said method comprising the steps of:

forming a gate wiring on an insulating surface;

forming a gate insulating film and an [initial] amorphous semiconductor film into a laminate sequentially without exposing them to an atmosphere on the gate wiring;

irradiating the [initial] amorphous semiconductor film with at least a light selected from the group consisting of an infrared light [or] and an ultraviolet light to crystallize the [initial] amorphous semiconductor film into a crystalline semiconductor film and to form an oxide film at a same time;

covering a first portion of the crystalline semiconductor film with a mask;

providing [a trivalent or pentavalent] an impurity element into second portions of the crystalline semiconductor film through the oxide film,

wherein the first portion of the crystalline semiconductor film is a channel forming region while the second portions of the crystalline semiconductor film are source and drain regions.

30 (Amended). A method according to claim 29,

wherein contaminants on a surface of the gate insulating film are reduced by active hydrogen or hydrogen compound before forming the [initial] amorphous semiconductor film.

33 (Amended). A method according to claim 29,

wherein the gate insulating film, the [initial] amorphous semiconductor film and the oxide film are formed in a same chamber.

34 (Amended). A method of fabricating an EL device, said method comprising the steps of:

forming a gate wiring on an insulating surface;

forming a gate insulating film, an [initial] amorphous semiconductor film, and an insulating film into a laminate sequentially without exposing them to an atmosphere on the gate wiring;

irradiating the [initial] amorphous semiconductor film with at least a light selected from the group consisting of an infrared light [or] and an ultraviolet light to crystallize the initial semiconductor film into a crystalline semiconductor film;

covering a first portion of the crystalline semiconductor film with a mask;

providing [a trivalent or pentavalent] an impurity element into second portions of the crystalline semiconductor film through the insulating film,

wherein the first portion of the crystalline semiconductor film is a channel forming region while the second portions of the crystalline semiconductor film are source and drain regions.

35 (Amended). A method according to claim 34,

wherein the gate insulating film, the [initial] amorphous semiconductor film, and the insulating film are formed in a same chamber.

36 (Amended). A method according to claim 34,

wherein contaminants on a surface of the gate insulating film are reduced by active hydrogen or hydrogen compound before forming the [initial] amorphous semiconductor film.